

PQMD12

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

8 July 2015

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor; for the PNP transis	or with negative polarity	,				,
V _{CEO}	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
Per transis	tor; for the PNP transis	or with negative polarity	,		'	'	
R1	resistance 1	T _{amb} = 25 °C		33	47	61	kΩ
R2/R1	resistance ratio			8.0	1	1.2	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	500	O1 I2 GND2
2	I1	input (base) TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$	
3	O2	output (collector) TR2	2 5	R1
4	GND2	GND (emitter) TR2		TR1 TR2
5	12	input (base) TR2	3 4	R2 R1
6	O1	output (collector) TR1	Transparent top view	
7	O1	output (collector) TR1	DFN1010B-6 (SOT1216)	GND1 I1 O2 aaa-007379
8	O2	output (collector) TR2		dad 557575

6. Ordering information

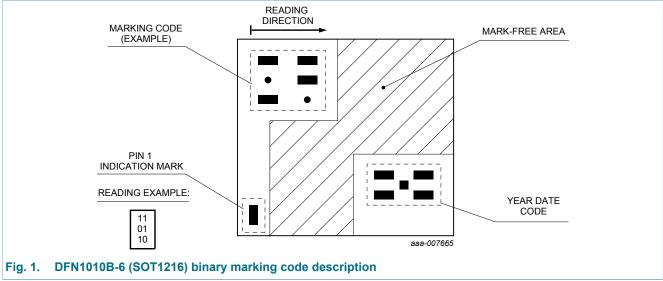
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PQMD12	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

7. Marking

Table 4. Marking codes

Type number	Marking code
PQMD12	11 00 00



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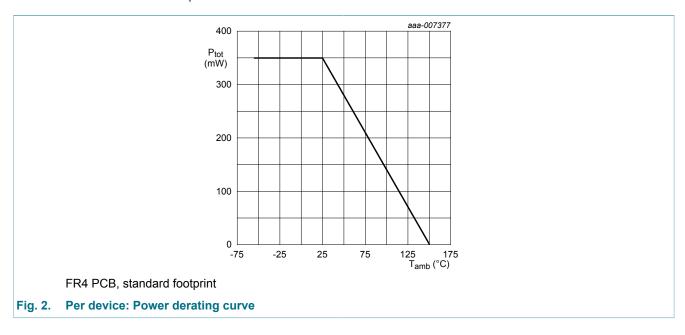
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor; for the PNP transistor with	negative polarity	'			
V_{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	10	V
VI	input voltage	TR1; positive		-	40	V
		TR1; negative		-	-10	V
		TR2; positive		-	10	V
		TR2; negative		-	-40	V
I _O	output current			-	100	mA
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse;		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	230	mW
Per device					'	,
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	350	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r						
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

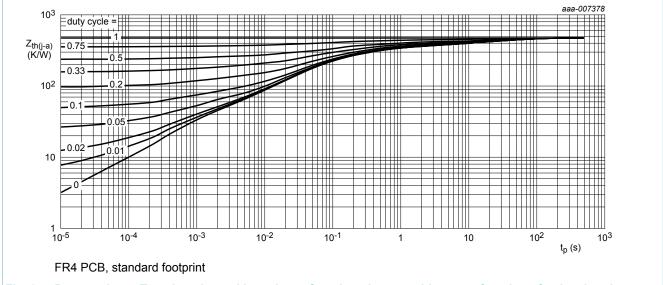


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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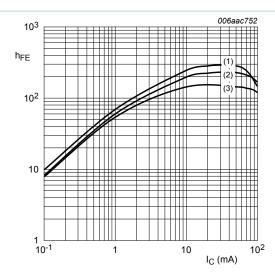
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor; for the PNP transistor	with negative polarity				'	
I _{CBO}	collector-base cut-off current (emitter open)	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μΑ
	current (base open)	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C		-	-	5	μA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	90	μA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 5 mA; T_{amb} = 25 °C		80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A; T_{amb} = 25 °C		-	1.2	0.8	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		3	1.6	-	V
R1	resistance 1	T _{amb} = 25 °C		33	47	61	kΩ
R2/R1	resistance ratio			0.8	1	1.2	
C _C	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; f = 1 \text{ MHz};$ $T_{amb} = 25 \text{ °C}; TR1 \text{ (NPN)}$		-	-	2.5	pF
		V_{CB} = -10 V; I_{E} = 0 A; f = 1 MHz; T_{amb} = 25 °C; TR2 (PNP)		-	-	3	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C; TR1 (NPN)	[1]	-	230	-	MHz
		V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C; TR2 (PNP)	[1]	-	180	-	MHz

^[1] Characteristics of built-in transistor

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



$$V_{CE} = 5 V$$

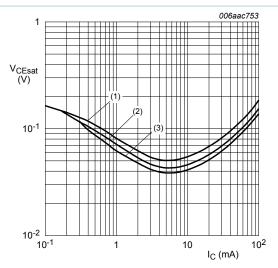
Fig. 4.

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = -40 °C



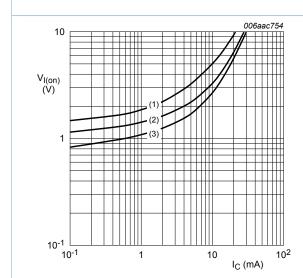


$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -40 \, ^{\circ}C$$



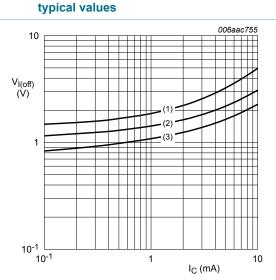
$$V_{CE}$$
 = 0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values



NPN transistor: Collector-emitter saturation

voltage as a function of collector current;

$$V_{CE} = 5 V$$

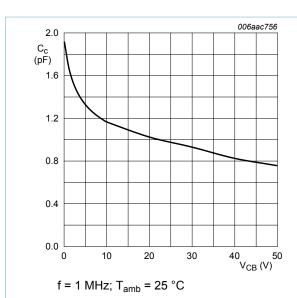
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

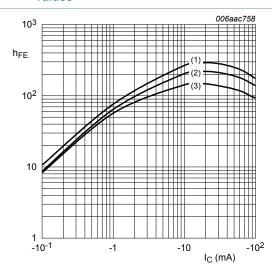
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values

NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



NPN transistor: Collector capacitance as a Fig. 8. function of collector-base voltage; typical values



 V_{CE} = -5 V

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

collector current; typical values

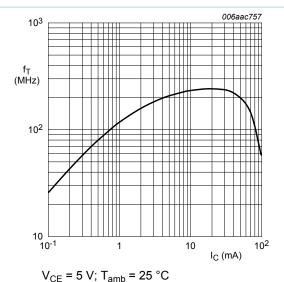
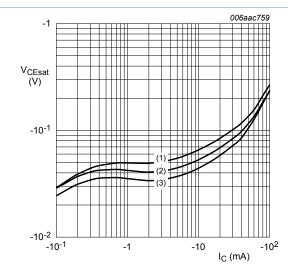


Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



 $I_{\rm C}/I_{\rm B} = 20$

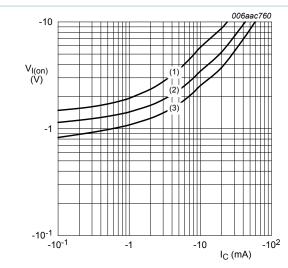
(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. PNP transistor: DC current gain as a function of Fig. 11. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

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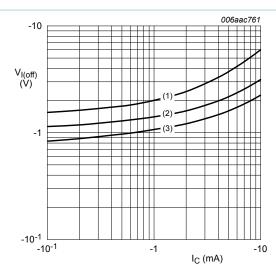
$$V_{CE}$$
 = -0.3 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 12. PNP transistor: On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 13. PNP transistor: Off-state input voltage as a function of collector current; typical values

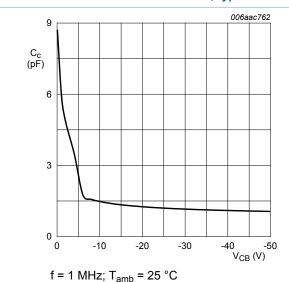


Fig. 14. PNP transistor: Collector capacitance as a function of collector-base voltage; typical

values of built-in transistor

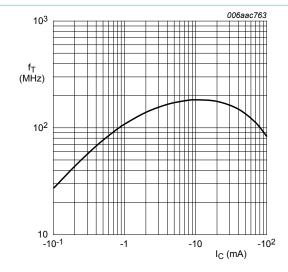


Fig. 15. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

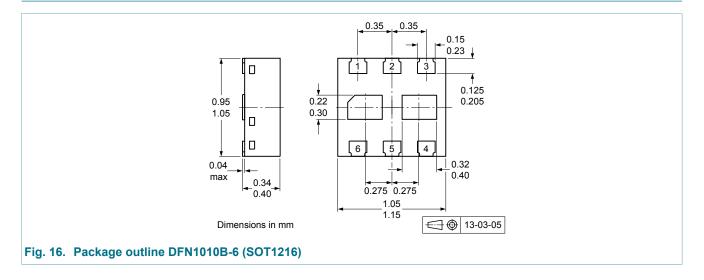
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11. Test information

11.1 Quality information

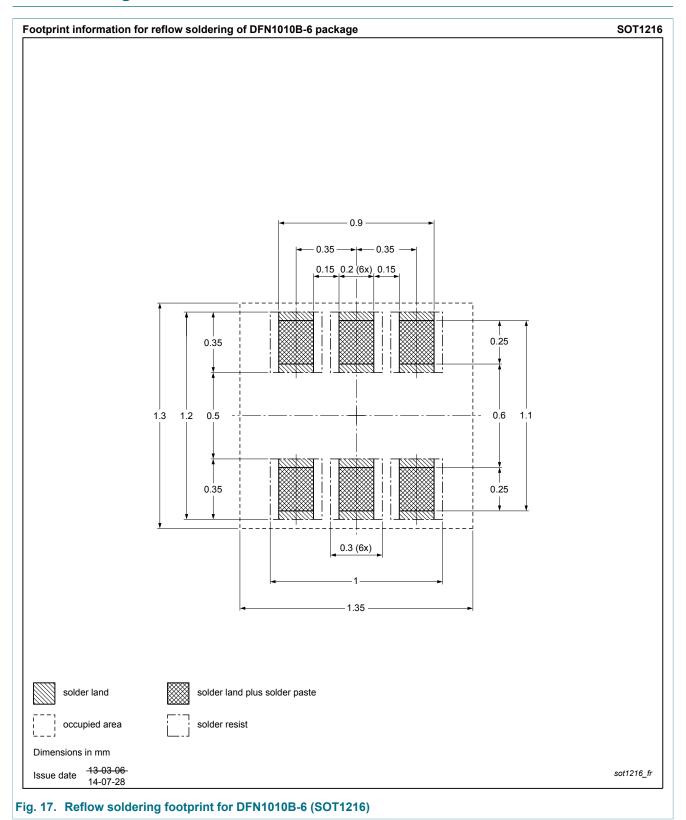
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



NPN/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PQMD12 v.2	20150708	Product data sheet	-	PQMD12 v.1
Modification:	Change of binary m	arking code position.		
PQMD12 v.1	20130724	Product data sheet	-	-

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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